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IDENTIFIER:

US 20030164354 A1

TITLE:

System level in-situ integrated dielectric etch process particularly useful for copper dual damascene

Detail Description Paragraph - DETX (73):

[0100] Increasing the RF power in the dielectric etch step increases the etch rate and improves microloading. It also adversely affects photoresist selectivity, striation and microtrenching, however. Higher pressures tend to improve microtrenching, etch rate, corner faceting and photoresist selectivity, but also tend to bow the etched profile. High Ar flows improve microloading while the absence of N.sub.2 gas generally give a bowing trench profile and lower photoresist selectivity. High Ar and/or N.sub.2 flows, however, create more faceting.